

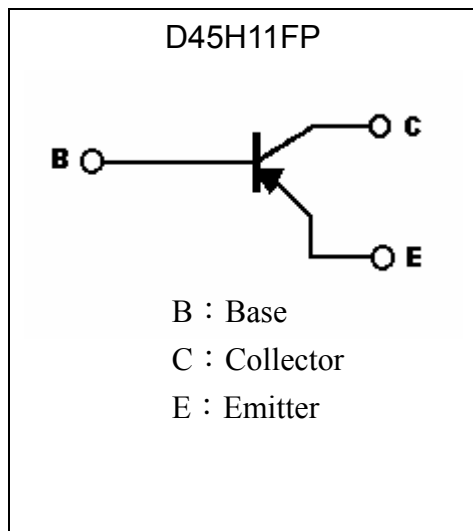
Low Vcesat PNP Epitaxial Planar Transistor

D45H11FP

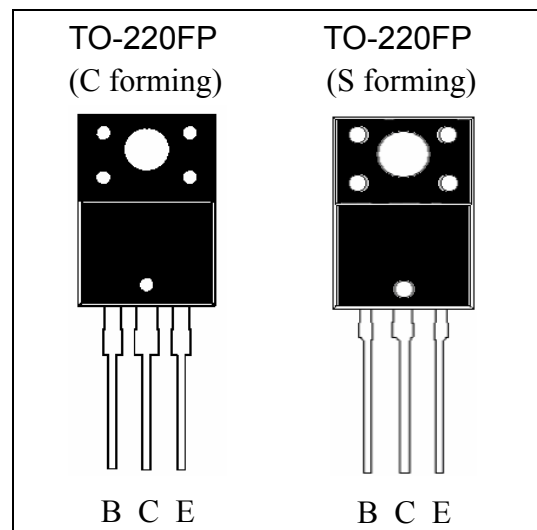
Features

- Low $V_{CE(sat)}$
- High BV_{CEO}
- Excellent current gain characteristics
- Pb-free lead plating package

Symbol

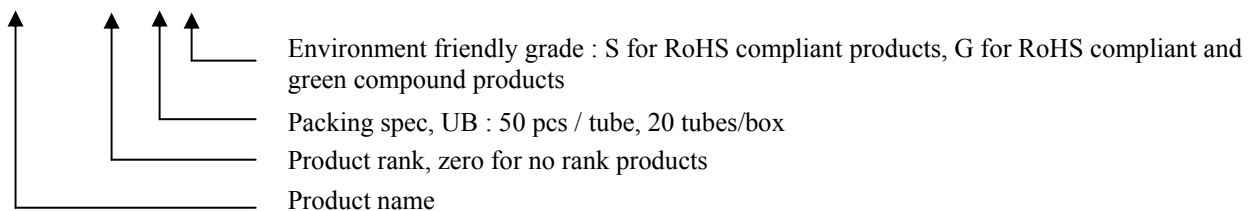


Outline



Ordering Information

Device	Package	Shipping
D45H11FP-0-UB-S	TO-220FP (RoHS compliant package)	50 pcs/tube, 20 tubes/box, 4 boxes / carton





Absolute Maximum Ratings (Ta=25°C)

Parameter	Symbol	Limits	Unit
Collector-Base Voltage	V _{CBO}	-80	V
Collector-Emitter Voltage	V _{CEO}	-80	V
Emitter-Base Voltage	V _{EBO}	-5	V
Collector Current (DC)	I _C	-10	A
Collector Current (Pulse)	I _{CP}	-20 (Note 1)	
Power Dissipation @ T _A =25°C	P _D	2	W
Power Dissipation @ T _C =25°C	P _D	50	
Thermal Resistance, Junction to Ambient	R _{θJA}	62.5	°C/W
Thermal Resistance, Junction to Case	R _{θJC}	2.5	°C/W
Junction Temperature	T _j	150	°C
Storage Temperature	T _{stg}	-55~+150	°C

Note : 1. Single Pulse , P_w ≤ 380μs, Duty ≤ 2%.

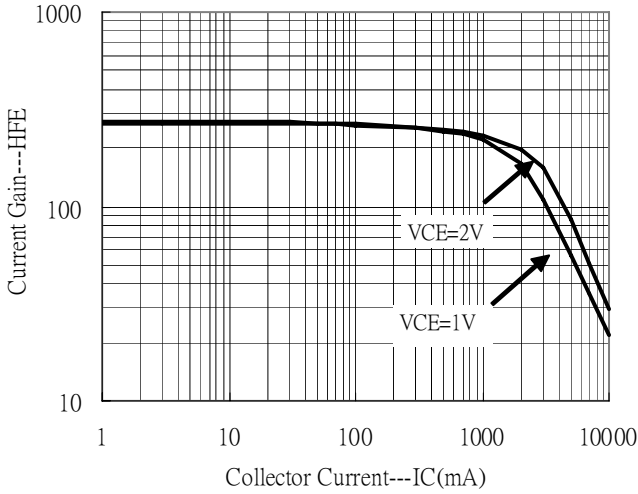
Characteristics (Ta=25°C)

Symbol	Min.	Typ.	Max.	Unit	Test Conditions
BV _{CEO(SUS)}	-80	-	-	V	I _C =-30mA, I _B =0
I _{CEO}	-	-	-10	μA	V _{CE} =-80V, I _B =0
I _{CES}	-	-	-10	μA	V _{CE} =-80V, V _{BE} =0
I _{EBO}	-	-	-50	μA	V _{EB} =-5V, I _C =0
*V _{CE(sat)}	-	-0.6	-1.0	V	I _C =-8A, I _B =-0.4A
*V _{BE(sat)}	-	-1.0	-1.5	V	I _C =-8A, I _B =-0.8A
*h _{FE}	60	-	-	-	V _{CE} =-1V, I _C =-2A
*h _{FE}	40	-	-	-	V _{CE} =-1V, I _C =-4A
f _T	-	40	-	MHz	V _{CE} =-10V, I _C =-500mA, f=20MHz
C _{ob}	-	230	-	pF	V _{CB} =-10V, f=1MHz

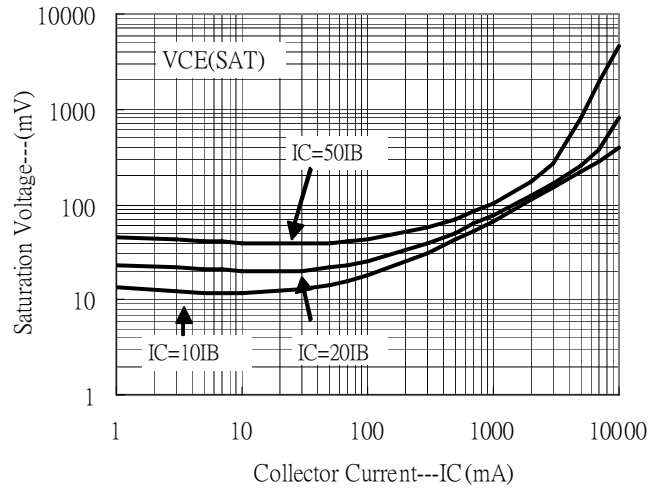
*Pulse Test : Pulse Width ≤ 380μs, Duty Cycle ≤ 2%

Typical Characteristics

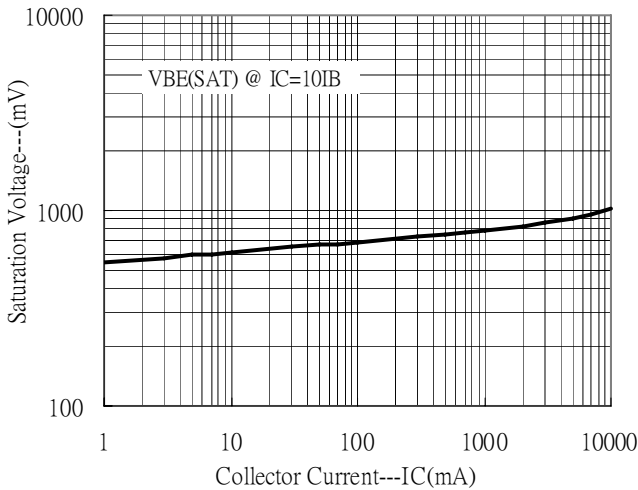
Current Gain vs Collector Current



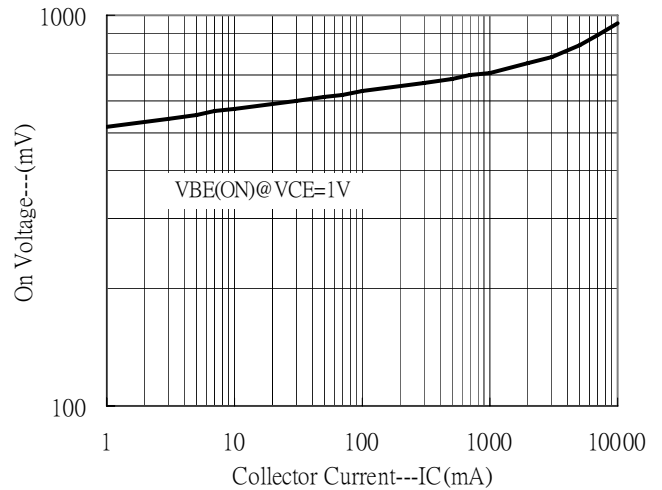
Saturation Voltage vs Collector Current



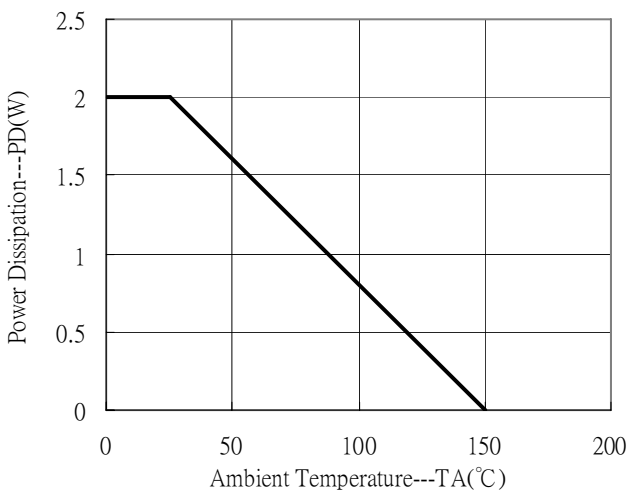
Saturation Voltage vs Collector Current



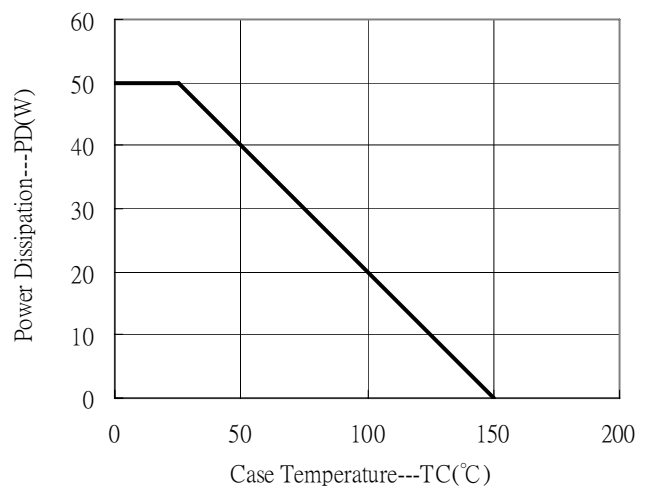
On Voltage vs Collector Current



Power Derating Curve



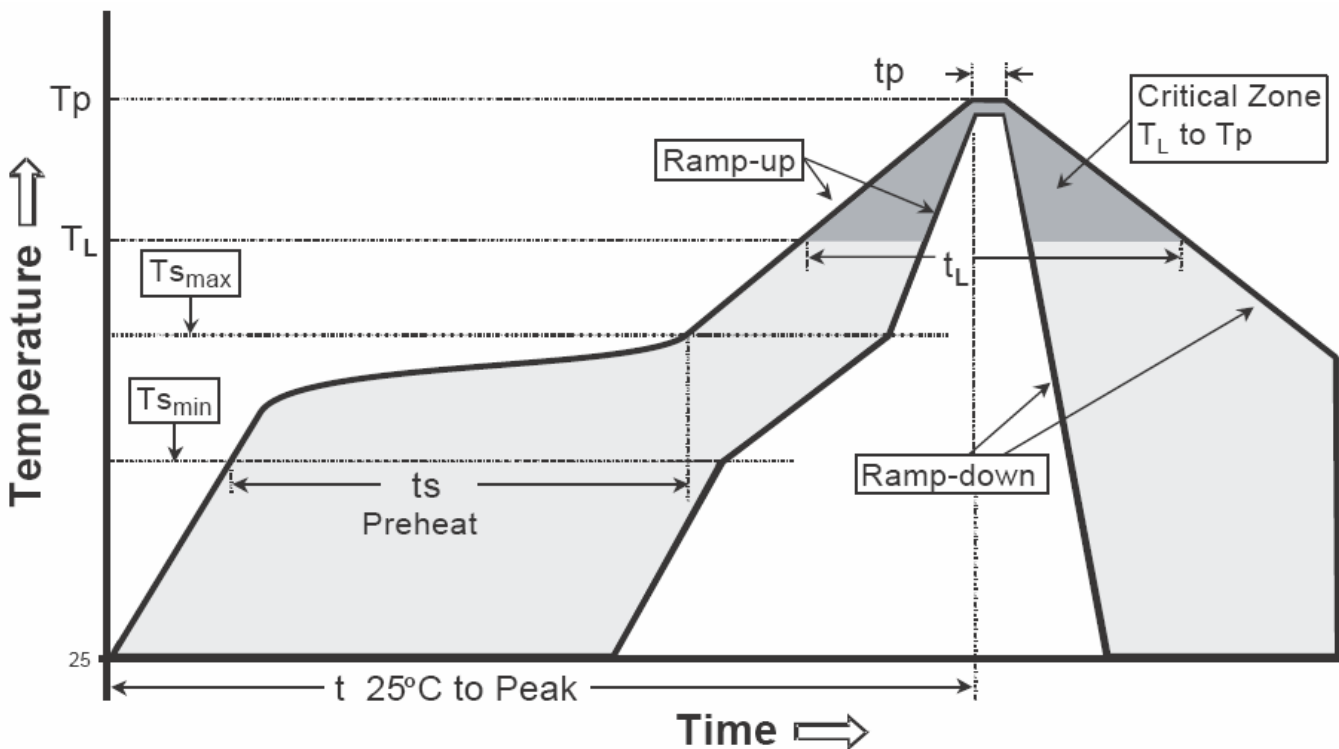
Power Derating Curve



Recommended wave soldering condition

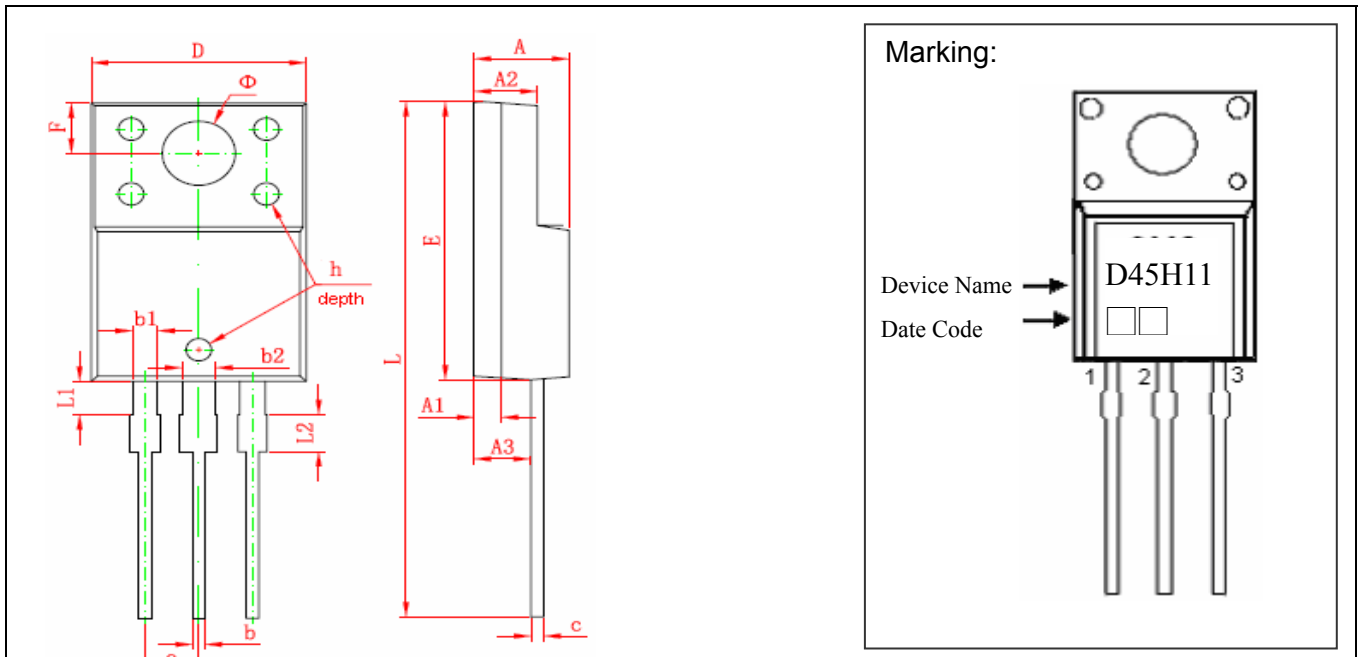
Product	Peak Temperature	Soldering Time
Pb-free devices	260 +0/-5 °C	5 +1/-1 seconds

Recommended temperature profile for IR reflow



Profile feature	Sn-Pb eutectic Assembly	Pb-free Assembly
Average ramp-up rate (T _{smax} to T _p)	3°C/second max.	3°C/second max.
Preheat		
-Temperature Min(T _{s min})	100°C	150°C
-Temperature Max(T _{s max})	150°C	200°C
-Time(t _{s min} to t _{s max})	60-120 seconds	60-180 seconds
Time maintained above:		
-Temperature (T _L)	183°C	217°C
- Time (t _L)	60-150 seconds	60-150 seconds
Peak Temperature(T _p)	240 +0/-5 °C	260 +0/-5 °C
Time within 5°C of actual peak temperature(t _p)	10-30 seconds	20-40 seconds
Ramp down rate	6°C/second max.	6°C/second max.
Time 25 °C to peak temperature	6 minutes max.	8 minutes max.

TO-220FP (C Forming) Dimension



3-Lead TO-220FP Plastic Package
CYStek Package Code: FP

Style: Pin 1.Base 2.Collector 3.Emitter

*Typical

DIM	Inches		Millimeters		DIM	Inches		Millimeters	
	Min.	Max.	Min.	Max.		Min.	Max.	Min.	Max.
A	0.169	0.185	4.300	4.700	E	0.583	0.598	14.800	15.200
A1	0.051 REF		1.300 REF		e	0.100*		2.540*	
A2	0.110	0.126	2.800	3.200	F	0.106 REF		2.700 REF	
A3	0.098	0.114	2.500	2.900	Φ	0.138 REF		3.500 REF	
b	0.020	0.030	0.500	0.750	h	0.000	0.012	0.000	0.300
b1	0.043	0.053	1.100	1.350	L	1.102	1.118	28.000	28.400
b2	0.059	0.069	1.500	1.750	L1	0.067	0.075	1.700	1.900
c	0.020	0.030	0.500	0.750	L2	0.075	0.083	1.900	2.100
D	0.392	0.408	9.960	10.360					

- Notes:** 1.Controlling dimension: millimeters.
 2.Maximum lead thickness includes lead finish thickness, and minimum lead thickness is the minimum thickness of base material.
 3.If there is any question with packing specification or packing method, please contact your local CYStek sales office.

Material:

- Lead: Pure tin plated.
- Mold Compound: Epoxy resin family, flammability solid burning class: UL94V-0.

TO-220FP (S Forming) Dimension

Marking:

Device Name → D45H11
 Date Code → [] [] []

Style: Pin 1.Base 2.Collector 3.Emitter

3-Lead TO-220FP Plastic Package
 CYStek Package Code: FP

*Typical

DIM	Inches		Millimeters		DIM	Inches		Millimeters	
	Min.	Max.	Min.	Max.		Min.	Max.	Min.	Max.
A	0.171	0.183	4.35	4.65	G	0.246	0.258	6.25	6.55
A1	0.051 REF		1.300 REF		H	0.138 REF	3.50 REF		
A2	0.112	0.124	2.85	3.15	H1	0.055 REF	1.40 REF		
A3	0.102	0.110	2.60	2.80	H2	0.256	0.272	6.50	6.90
b	0.020	0.030	0.50	0.75	J	0.031 REF		0.80 REF	
b1	0.031	0.041	0.80	1.05	K	0.020		0.50 REF	
b2	0.047 REF		1.20 REF		L	1.102	1.118	28.00	28.40
c	0.020	0.030	0.500	0.750	L1	0.043	0.051	1.10	1.30
D	0.396	0.404	10.06	10.26	L2	0.036	0.043	0.92	1.08
E	0.583	0.598	14.80	15.20	M	0.067 REF		1.70 REF	
e	0.100 *		2.54*		N	0.012 REF		0.30 REF	
F	0.106 REF		2.70 REF						

Notes: 1.Controlling dimension: millimeters.
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Material:

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- Mold Compound: Epoxy resin family, flammability solid burning class: UL94V-0.

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